

AMENDMENT

U.S. Application No.: 09/321,605

cont, B
-> forming an oxide dielectric film of the capacitor on the lower electrode;
forming an upper electrode of the capacitor on the oxide dielectric film;
forming a second insulating film for covering the capacitor;
forming a first opening which exposes the impurity diffusion layer and a second opening which exposes the upper electrode in the first and second insulating films, by etching a part of the second insulating film and a part of the first insulating film;
forming a metal film on the second insulating film for connecting electrically the impurity diffusion layer via the first opening and the upper electrode via the second opening;
forming a local interconnection covering an entire portion of the upper electrode with an area which is larger than an area where the upper electrode contacts with the oxide dielectric film, in a range which passes through the first opening and the second opening, by patterning the metal film; and
forming a third insulating film for covering the local interconnection.

Claim 2, line 2 delete "the" and substitute therefore --an--.

Sub C3
B2
21. (Amended) A method of manufacturing a semiconductor device comprising the steps of:
forming an impurity diffusion layer in a semiconductor substrate;
forming a first insulating film covering the semiconductor substrate;
forming a lower electrode of a capacitor on the first insulating film;

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forming an oxide dielectric film of the capacitor on the lower electrode;
forming an upper electrode of the capacitor on the oxide dielectric film;
forming a second insulating film for covering the capacitor;
forming a first opening which exposes the impurity diffusion layer and a second opening which exposes the upper electrode in the first and second insulating films, by etching a part of the second insulating film and a part of the first insulating film;

forming a metal film on the second insulating film for connecting electrically the impurity diffusion layer via the first opening and the upper electrode via the second opening;

forming a local interconnection covering an entire portion of the upper electrode with an area which is larger than an area where the upper electrode contacts with the oxide dielectric film, in a range which passes through the first opening and the second opening, by patterning the metal film, wherein the local interconnection is a blocking layer for preventing a diffusion of a redundant to the oxide dielectric film; and

forming a third insulating film for covering the local interconnection.